



JRW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Soo-doo CHAE, et al.

Art Unit: 2818

Serial No. 10/681,346

Examiner: Dung Anh Le

Filed: October 9, 2003

Confirmation No. 8321

For: METHOD FOR MANUFACTURING A SINGLE
ELECTRON MEMORY DEVICE HAVING
QUANTUM DOTS BETWEEN A GATE
ELECTRODE AND A SINGLE ELECTRON
STORAGE ELEMENT (As Amended)

Attorney Docket No. 249/286 DIV

**AMENDMENT UNDER 37 C.F.R. § 1.111 AFTER CLOSE OF PROSECUTION
ON THE MERITS UNDER *EX PARTE QUAYLE***

Mail Stop Amendment
Commissioner for Patents
United States Patent and Trademark Office
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

INTRODUCTORY COMMENTS

In response to the Office action mailed July 1, 2004, please amend the above-identified application as follows:

Amendments to the Specification begin on page 2 of this paper.

Remarks begin on page 3 of this paper.

A replacement Abstract of the Disclosure is attached at page 5 of this paper.